

STL73

MEDIUM VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- n MEDIUM VOLTAGE CAPABILITY
- n LOW SPREAD OF DYNAMIC PARAMETERS
- n MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- n VERY HIGH SWITCHING SPEED

APPLICATIONS

COMPACT FLUORESCENT LAMPS (CFLS)

DESCRIPTION

The device is manufactured using high voltage Multi-Epitaxial Planar technology for high switching speeds and medium voltage capability.

It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

The STL series is designed for use in Compact Fluorescent Lamps.



Figure 2: Internal Schematic Diagram

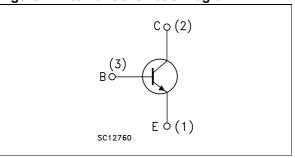


Table 1: Order Codes

Part Number	Marking	Package	Packaging
STL73	L73 L or (#) L73 H	TO-92	Bulk

[#] See:note on page 2

Table 2: Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{CES} Collector-Emitter Voltage (V _{BE} = 0)		700	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	400	V
V_{EBO}	Emitter-Base Voltage (I _C = 0)	V _{(BR)EBO}	V
I _C	Collector Current	1.5	Α
I _{CM}	Collector Peak Current (t _p < 5ms)	3	Α
Ι _Β	Base Current	0.5	Α
I _{BM}	Base Peak Current (t _p < 5ms)	1.5	Α
P _{tot}	Total Dissipation at T _C = 25 °C	1.1	W
T _{stg}	Storage Temperature	-65 to 150	°C
TJ	Max. Operating Junction Temperature	150	°C

Table 3: Thermal Data

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Table 4: Electrical Characteristics (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Co	onditions	Min.	Тур.	Max.	Unit
I _{CEV}	Collector Cut-off Current	V _{CE} = 700 V				1	mA
	(V _{BE} = -1.5 V)	V _{CE} = 700 V	T _j = 125 °C			5	mA
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	i _E = 10 mA		9		18	V
	$(I_C = 0)$						
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage	I _C = 10 mA		400			V
	$(I_B = 0)$						
V _{CE(sat)} *	Collector-Emitter	I _C = 0.3 A	I _B = 60 mA		0.15	0.4	V
	Saturation Voltage	I _C = 0.6 A	I _B = 120 mA		0.25	0.6	V
		I _C = 1 A	I _B = 250 mA		0.4	1	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 0.6 A	I _B = 120 mA		0.95	1.1	V
h _{FE}	DC Current Gain #	I _C = 0.6 A	V _{CE} = 3 V				
		Group L		10		16	
		Group H		15		21	
		I _C = 1.5 A	$V_{CE} = 5 V$	4		10	
	RESISTIVE LOAD	I _C = 1	V _{CC} = 125 V				
t_f	Rise Time	I _{B1} = -I _{B2} = 200 mA	t _p = 25 μs			1	μs
	Storage Time	(see figure 4)				4	μs
	Fall Time	, , , , , , , , , , , , , , , , , , ,				0.7	μs
	INDUCTIVE LOAD	I _C = 0.3	V _{Clamp} = 300 V				
t_f	Fall Time	$I_{B1} = -I_{B2} = 60 \text{ mA}$	L = 3 mH		0.3		μs
		(see figure 3)					

^{*} Pulsed: Pulsed duration = 300 $\mu s,$ duty cycle ≤ 1.5 %.

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[#] The product is pre-selected in DC current gain (Group L and Group H). STMicroelectronics reserves the right to ship either groups according to production availability. Please contact your nearest STMicroelectronics sales office for delivery datails.

Figure 3: Inductive Load Switching Test Circuit

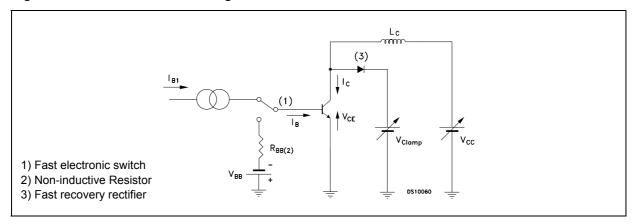
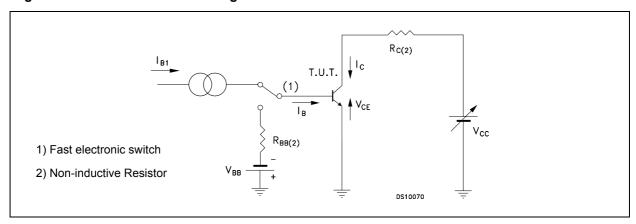
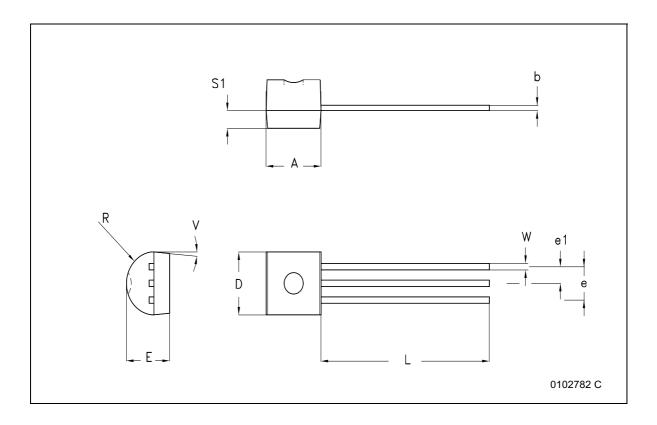


Figure 4: Restistive Load Switching Test Circuit



TO-92 BULK SHIPMENT MECHANICAL DATA

DIM	mm.					
DIM.	MIN.	ТҮР	MAX.			
А	4.32		4.95			
b	0.36		0.51			
D	4.45		4.95			
E	3.30		3.94			
е	2.41		2.67			
e1	1.14		1.40			
L	12.70		15.49			
R	2.16		2.41			
S1	0.92		1.52			
W	0.41		0.56			
V		5 ^O				



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Figure 5: Revision History

Release Date	Version	Change Designator
11-Jul-2005	1	First Release.

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